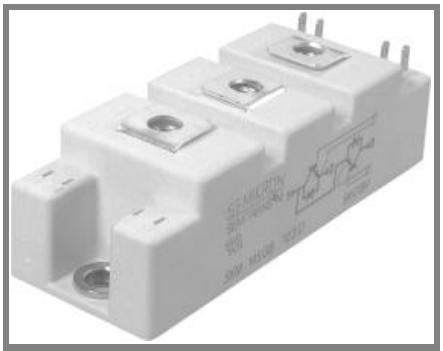
SKM 75GB173D



SEMITRANS® 2

IGBT Modules

SKM 75GB173D

Features

- N channel, Homogeneous Si
- Low inductance case
- Very low tail current with low temperature dependence
- High short circuit capability, self limiting to 6 x I_{cnom}
- Latch-up free
- Fast & soft inverse CAL diodes
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- Large clearance (10 mm) and creepage distance (20 mm)

Typical Applications

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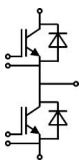
- DC bus voltage 750 - 1200 V_{DC}
- Public transport (auxiliary syst.)
- Switching (not for linear use)



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Absolute Maximum Ratings			T_c = 25 °C, unless otherwise specified	
Symbol	**Conditions**		**Values**	**Units**
IGBT				
V_{CES}	T_j = 25 °C		1700	V
I_C	T_j = 150 °C	T_{case} = 25 °C	75	A
		T_{case} = 80 °C	50	A
I_{CRM}	I_{CRM}=2xI_{Cnom}		100	A
V_{GES}			± 20	V
t_{psc}	V_{CC} = 1200 V; $V_{GE} \leq$ 20 V; V_{CES} < 1700 V	T_j = 125 °C	10	µs
Inverse Diode				
I_F	T_j = 150 °C	T_{case} = 25 °C	60	A
		T_{case} = 80 °C	40	A
I_{FRM}	I_{FRM}=2xI_{Fnom}		100	A
I_{FSM}	t_p = 10 ms; sin.	T_j = 150 °C	550	A
Module				
$I_{t(RMS)}$			200	A
T_{vj}			- 40 ... + 150	°C
T_{stg}			-40...+125	°C
V_{isol}	AC, 1 min.		4000	V

Characteristics			T_c = 25 °C, unless otherwise specified			
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
IGBT						
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 4 mA		4,8	5,5	6,2	V
I_{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T_j = 25 °C		0,1	0,3	mA
V_{CE0}		T_j = 25 °C		1,65	1,9	V
		T_j = 125 °C		1,9	2,15	V
r_{CE}	V_{GE} = 20 V	T_j = 25°C		35	40	mΩ
		T_j = 125°C		46	57	mΩ
$V_{CE(sat)}$	I_{Cnom} = 50 A, V_{GE} = 15 V	T_j = 25°C$_{chiplev.}$		3,4	3,9	V
		T_j = 125°C$_{chiplev.}$		4,2	5	V
C_{ies}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		8		nF
C_{oes}				0,64		nF
C_{res}				0,25		nF
Q_G	V_{GE} = -8V...+15V			650		nC
$t_{d(on)}$	R_{Gon} = 12 Ω	V_{CC} = 1200V I_{Cnom}= 50A T_j = 125 °C V_{GE} = ± 15V		40		ns
t_r				35		ns
E_{on}				18		mJ
$t_{d(off)}$	R_{Goff} = 12 Ω			400		ns
t_f				58		ns
E_{off}				13		mJ
$R_{th(j-c)}$	per IGBT				0,25	K/W

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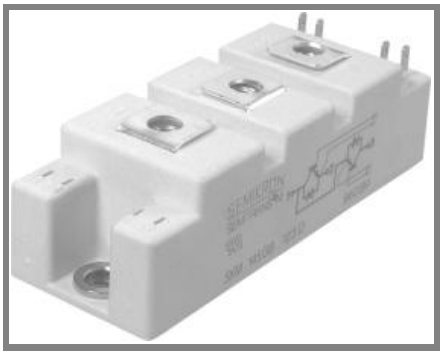

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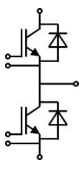

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Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
Inverse Diode						
$V_F = V_{EC}$	I_{Fnom} = 50 A; V_{GE} = 0 V	T_j = 25 °$C_{chiplev.}$		2,2	2,7	V
		T_j = 125 °$C_{chiplev.}$		2	2,4	V
V_{F0}		T_j = 125 °C		1,3	1,5	V
r_F		T_j = 125 °C		12	18	mΩ
I_{RRM}	I_{Fnom} = 50 A	T_j = 125 °C		43		A
Q_{rr}	di/dt = 800 A/µs			15		µC
E_{rr}	V_{GE} = -15 V; V_{CC} = 1200 V					mJ
$R_{th(j-c)D}$	per diode				0,75	K/W
Module						
L_{CE}					30	nH
$R_{CC'+EE'}$	res., terminal-chip	T_{case}= 25 °C		0,75		mΩ
		T_{case}= 125 °C		1		mΩ
$R_{th(c-s)}$	per module				0,05	K/W
M_s	to heat sink M6		3		5	Nm
M_t	to terminals M5		2,5		5	Nm
w					160	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

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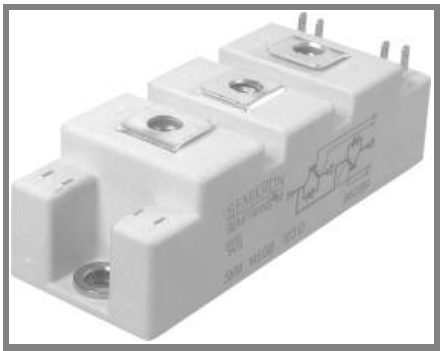

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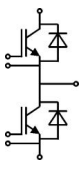

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Z_{th} Symbol	Conditions	Values	Units
$Z_{th(j-c)I}$			
R_i	i = 1	190	mk/W
R_i	i = 2	35	mk/W
R_i	i = 3	17	mk/W
R_i	i = 4	8	mk/W
tau_i	i = 1	0,1319	s
tau_i	i = 2	0,0042	s
tau_i	i = 3	0,0018	s
tau_i	i = 4	0,0003	s
$Z_{th(j-c)D}$			
R_i	i = 1	530	mk/W
R_i	i = 2	170	mk/W
R_i	i = 3	45	mk/W
R_i	i = 4	5	mk/W
tau_i	i = 1	0,0839	s
tau_i	i = 2	0,0069	s
tau_i	i = 3	0,0069	s
tau_i	i = 4	0,0005	s

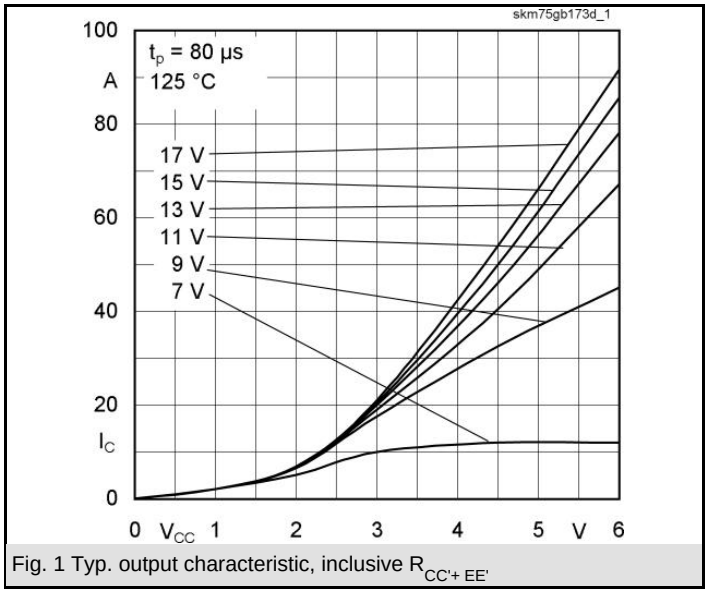

Fig. 1 Typ. output characteristic, inclusive $R_{CC'+EE'}$

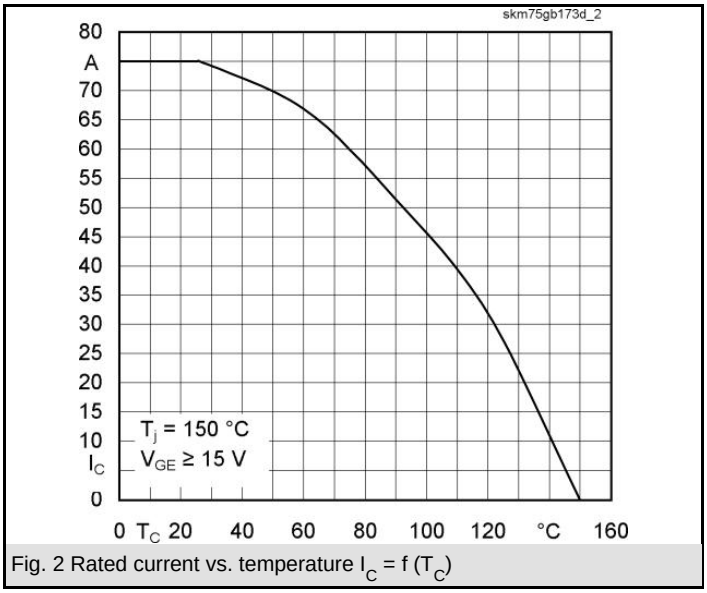

Fig. 2 Rated current vs. temperature $I_C = f(T_C)$

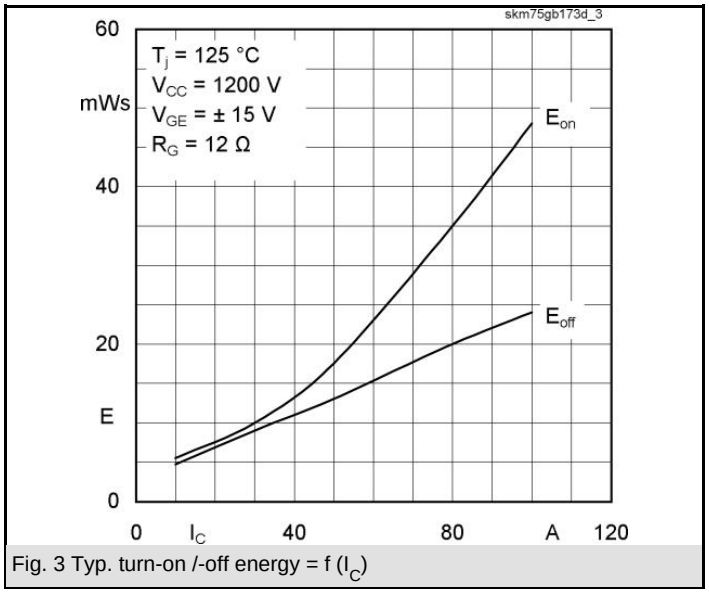

Fig. 3 Typ. turn-on /-off energy = f (I_C)

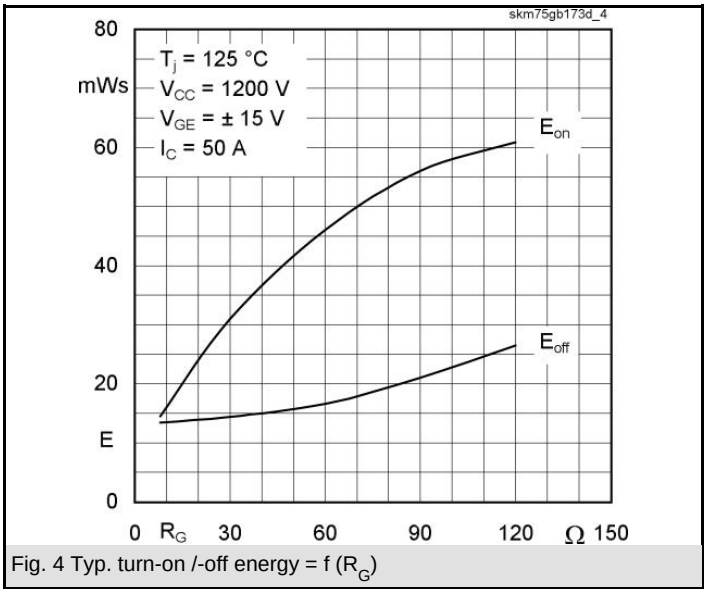

Fig. 4 Typ. turn-on /-off energy = f (R_G)

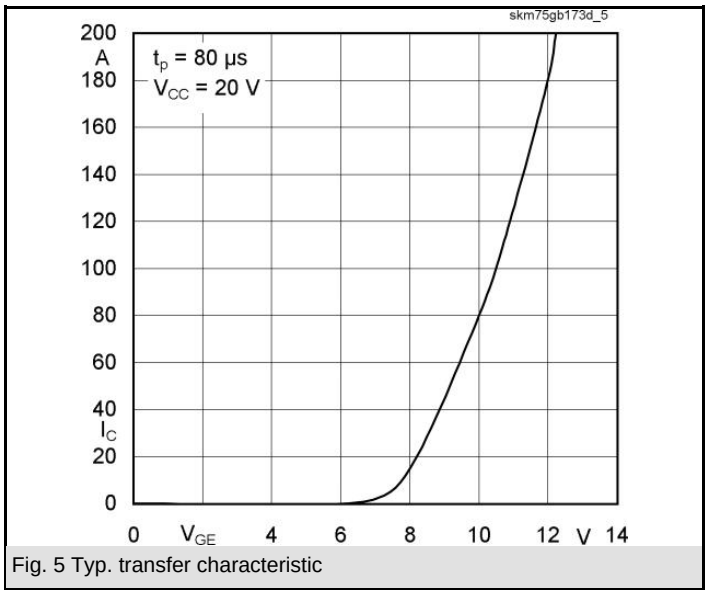

Fig. 5 Typ. transfer characteristic

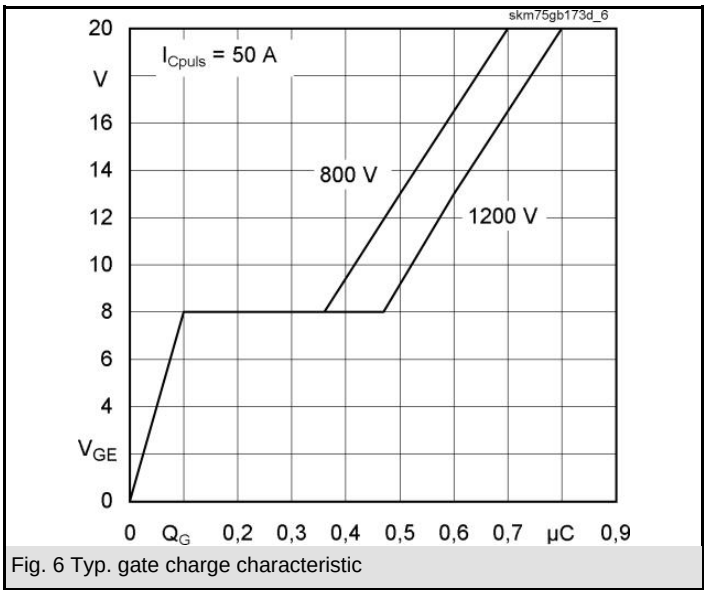

Fig. 6 Typ. gate charge characteristic

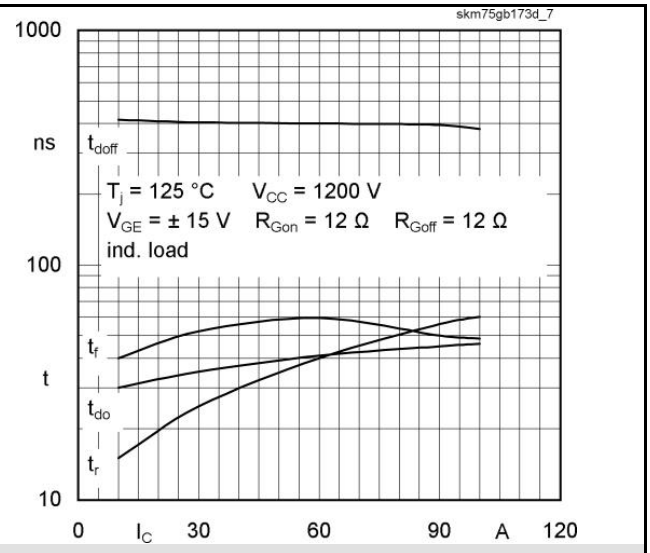

Fig. 7 Typ. switching times vs. I_C

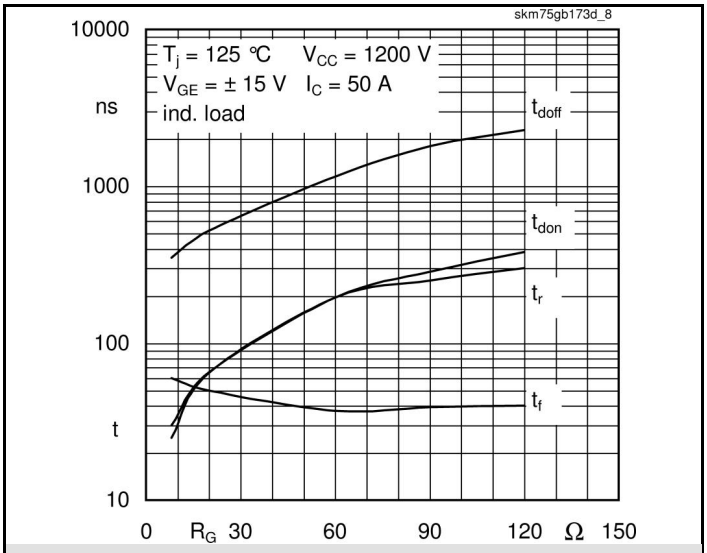

Fig. 8 Typ. switching times vs. gate resistor R_G

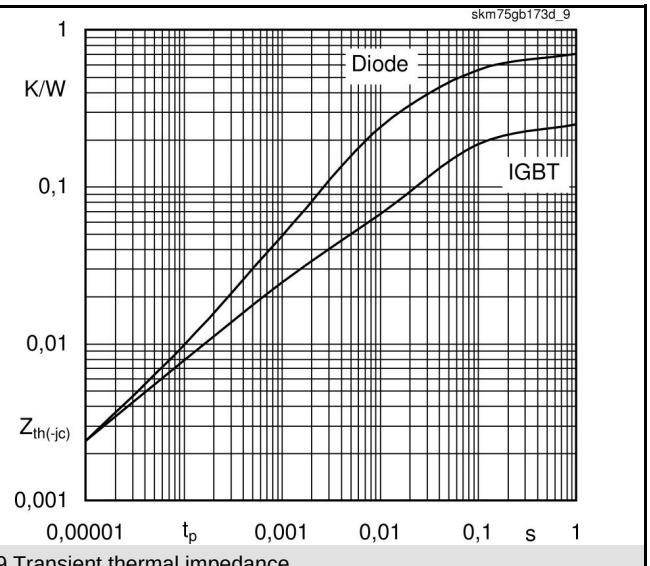

Fig. 9 Transient thermal impedance

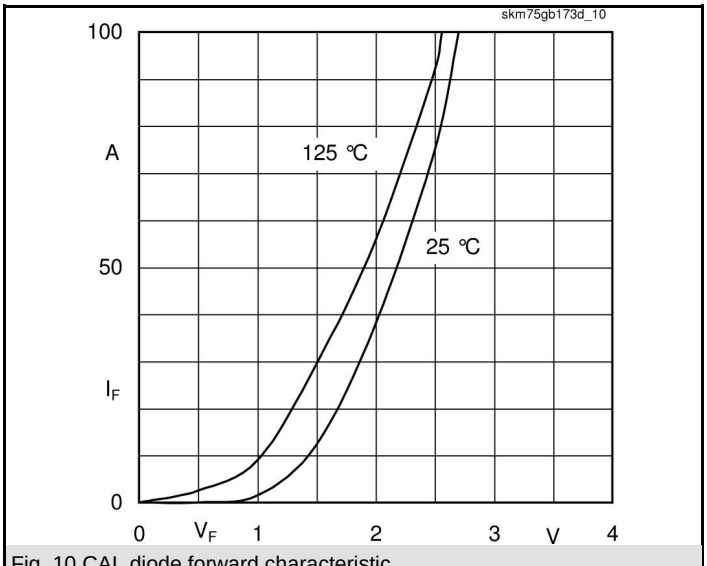

Fig. 10 CAL diode forward characteristic

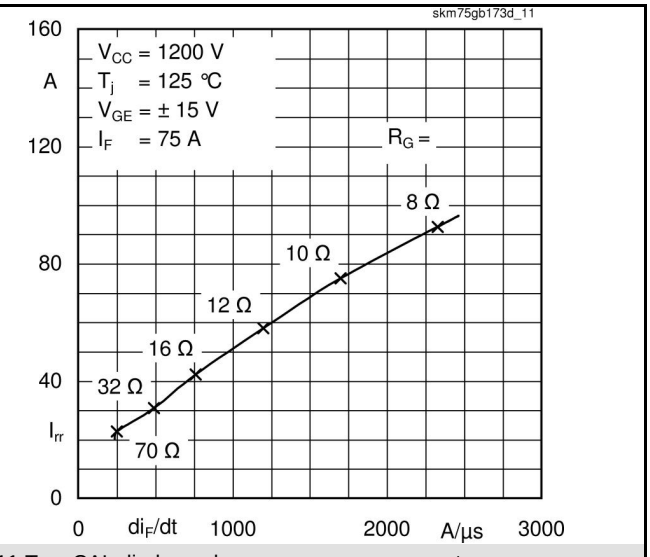

Fig. 11 Typ. CAL diode peak reverse recovery current

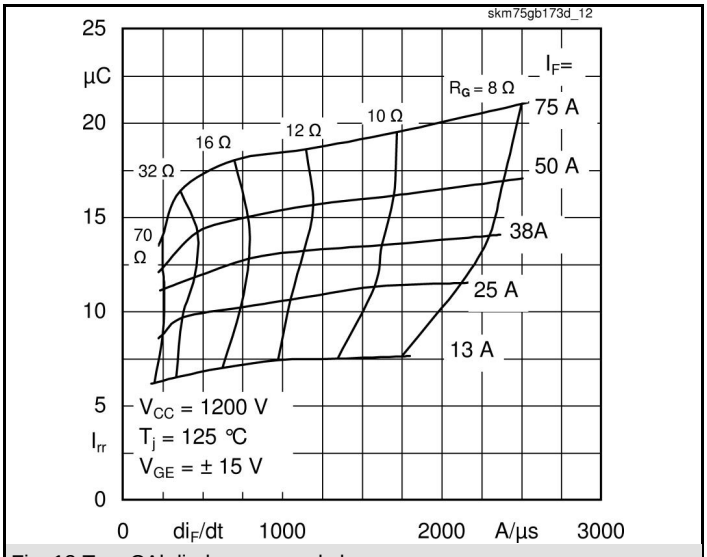

Fig. 12 Typ. CAl diode recovered charge

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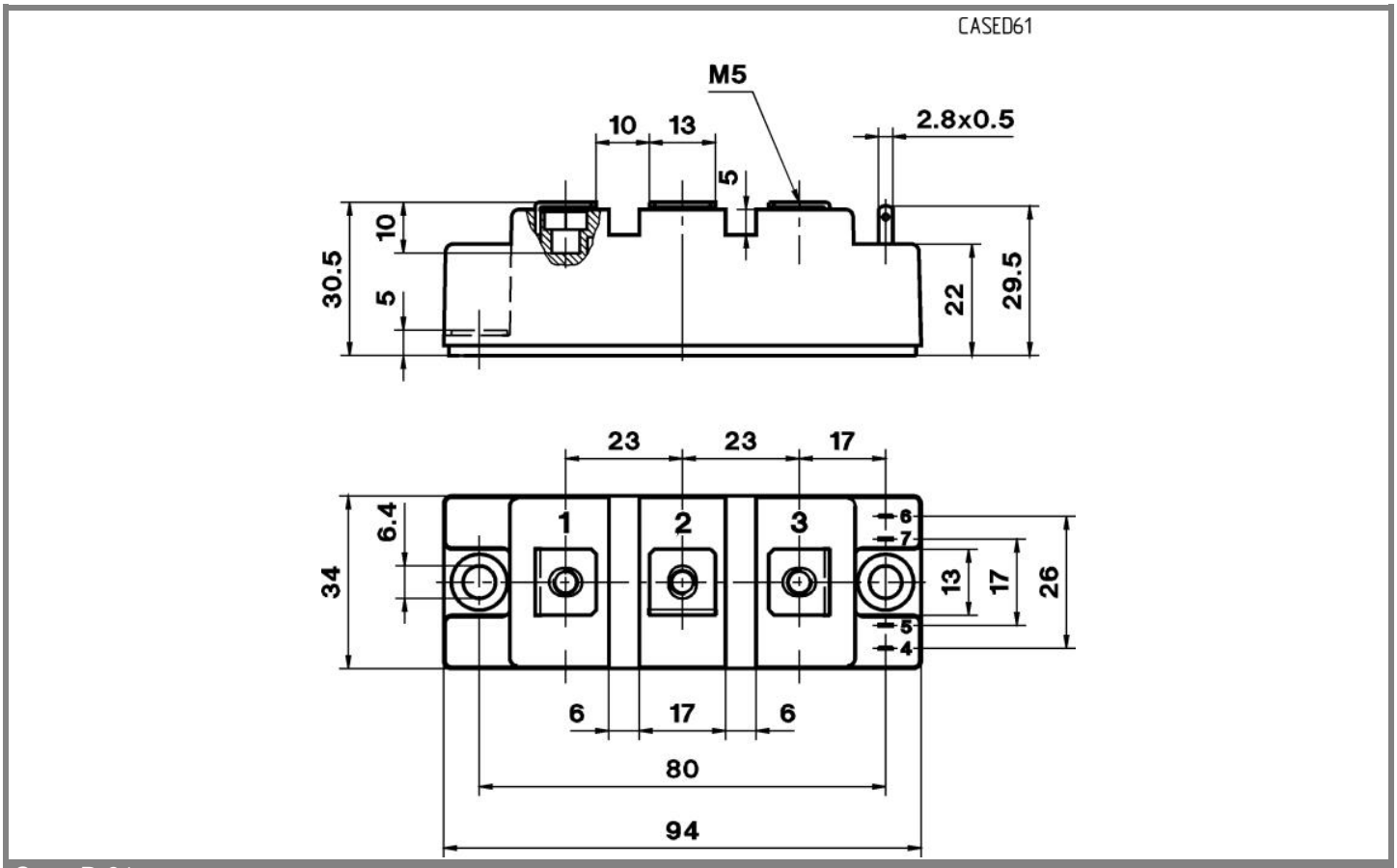
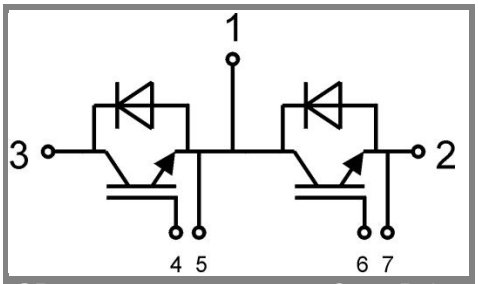


Case D 61



GB Case D 61

